

Pages 1 to 18

TRANSISTORS, HIGH POWER, NPN

BASED ON TYPE 2N5154

ESCC Detail Specification No. 5203/010





ISSUE 3 - Draft A

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2006. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No	. CHANGE DESCRIPTION
187 TBI	Specification up issued to incorporate editorial and technical changes per DCR.



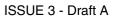




TABLE OF CONTENTS

<u>1.</u>	GENERAL	<u>5</u>
1.1	Scope	5
1.2	Applicable Documents	5
1.3	Terms, Definitions, Abbreviations, Symbols and Units	5
1.4	The ESCC Component Number and Component Type Variants	5
1.4.1	The ESCC Component Number	5
1.4.2	Component Type Variants	5
1.5	Maximum Ratings	5
1.6	Handling Precautions	7
1.7	Physical Dimensions and Terminal Identification	8
1.7.1	Metal Can Package (TO-39) - 3 lead	8
1.7.2	Metal Flange Mount Package (TO-257) - 3 lead	9
1.7.3	Surface Mount Package (SMD.5) - 3 terminal	10
1.8	Functional Diagram	11
1.9	Materials and Finishes	11
<u>2.</u>	REQUIREMENTS	<u>11</u>
2.1	General	11
2.1.1	Deviations from the Generic Specification	12
2.1.1.1	Deviation from Screening Tests - Chart F3	12
2.1.1.2	Deviation from Qualification and Periodic Tests - Chart F4	12
2.2	Marking	12
2.3	Terminal Strength	12
2.4	Verification of Safe Operating Area	12
2.5	Electrical Measurements at Room, High and Low Temperatures	12
2.5.1	Room Temperature Electrical Measurements	12
2.5.2	High and Low Temperatures Electrical Measurements	15
2.6	Parameter Drift Values	16
2.7	Intermediate and End-Point Electrical Measurements	16
2.8	Power Burn-in Conditions	16
2.8.1	Power Burn-in Conditions (TO-39)	16
2.8.2	Power Burn-in Conditions (TO-257 and SMD.5)	17
2.9	Operating Life Conditions	17
APPENDIX '/	۹٬	18



1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows:

Example: 520301001

• Detail Specification Reference: 5203010

Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and Finish	Weight max g
01	2N5154	TO-39	D2	1.5
02	2N5154	TO-39	D3 or D4	1.5
04	2N5154	TO-257	H2	5
05	2N5154	TO-257	H4	5
06	2N5154	SMD.5	Q14	2

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage. Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.



Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V _{CBO}	100	V	Over T _{op}
Collector-Emitter Voltage	V _{CEO}	80	V	Over T _{op} Note 5
Emitter-Base Voltage	V _{EBO}	6	V	Over T _{op}
Collector Current	Ic	5	Α	Continuous Note 5
Base Current	I _B	1	Α	Continuous
Power Dissipation For TO-39 For TO-257 and SMD.5	P _{tot1}	1 3.3	w	At T _{amb} ≤ +25°C Note 1
For TO-39 For TO-257 and SMD.5	P _{tot2}	8.75 35	W	At T _{case} ≤ +25°C Note 1
Operating Temperature Range	T _{op}	-65 to +200	°C	Note 2
Storage Temperature Range	T _{stg}	-65 to + 200	°C	Note 2
Soldering Temperature For TO-39 and TO-257 For SMD.5	T _{sol}	+260 +245	°C	Note 3 Note 4
Thermal Resistance Junction to Case For TO-39	R _{th(j-c)}	20	°C/W	
For TO-257 and SMD.5		5		

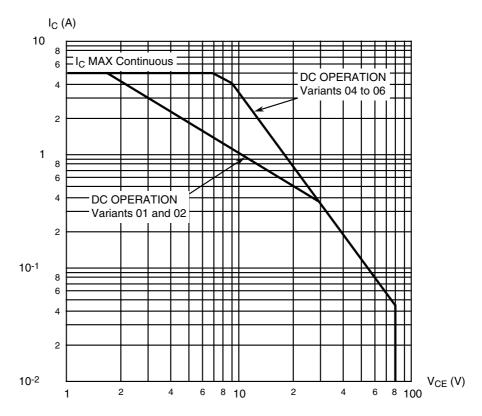
- For T_{amb} or T_{case} > +25°C, derate linearly to 0W at +200°C.
 For Variants with tin-lead plating or hot solder dip lead finish all testing performed at T_{amb} > +125°C shall be carried out in a 100% inert atmosphere.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same package shall not be resoldered until 3 minutes have



elapsed.

5. Safe Operation Area applies as follows:

Maximum Safe Operating Area Graph



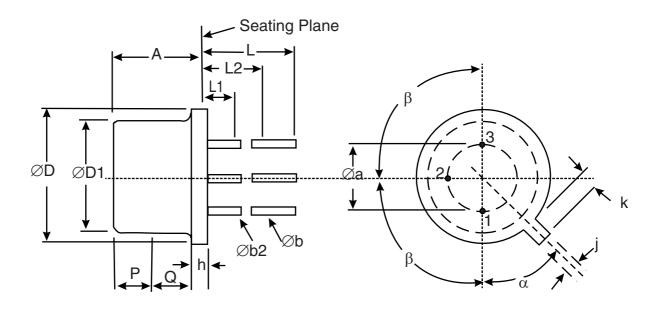
1.6 <u>HANDLING PRECAUTIONS</u>

The TO-257 package contains Beryllium Oxide (BeO) and therefore it must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.



1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 <u>Metal Can Package (TO-39) - 3 lead</u>



Symbols	Dimension	Notes	
Symbols	Min	Max	Notes
Øa	4.83	5.35	
Α	6	6.6	
Øb	0.4	0.533	2, 3
Øb2	0.4	0.483	2, 3
ØD	8.31	9.4	
ØD1	7.75	8.51	5
h	0.229	3.18	
j	0.711	0.864	
k	0.737	1.14	4
L	12.7	19	2
L1	-	1.27	2, 3
L2	6.35	-	2, 3
Р	2.54	-	5
Q	-	-	6
α	45° E	BSC	1, 7
β	90° E	BSC	1

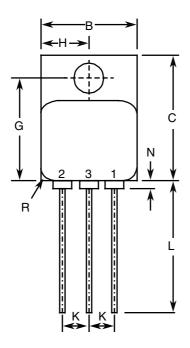
NOTES:

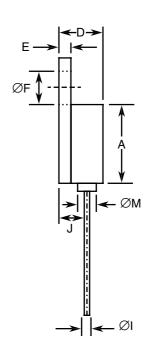
1. Terminal identification is specified by reference to the tab position where Lead 1 = emitter, Lead 2



- = base and Lead 3 = collector.
- 2. Applies to all leads.
- 3. Øb2 applies between L1 and L2. Øb applies between L2 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
- 4. Measured from the maximum diameter of the actual device.
- 5. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
- 6. The details of outline in this zone are optional.
- 7. Measured from the tab centreline.

1.7.2 <u>Metal Flange Mount Package (TO-257) - 3 lead</u>





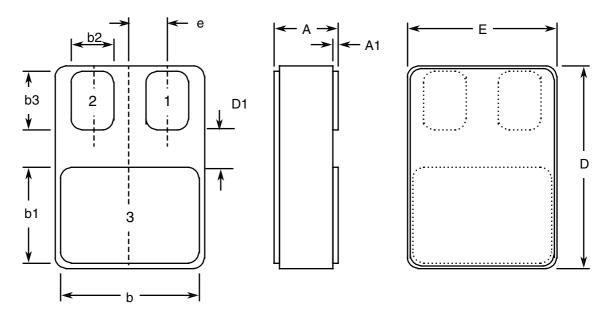
Symbols	Dimension	Notes	
Symbols	Min	Max	Notes
Α	10.41	10.67	
В	10.41	10.67	
С	16.51	16.76	
D	4.7	5.33	
E	0.89	1.14	
ØF	3.56	3.81	
G	13.39	13.64	
Н	5.13	5.38	
ØI	0.64	0.89	2
J	2.92	3.16	
К	2.41	2.67	
L	15.24	16.51	



Symbols	Dimension	Notes	
	Min	Max	Notes
ØM	2.29 T	2	
N	- 0.71		2
R	1.65 T	3	

- 1. Terminal identification is specified by the component's geometry where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
- 2. Applies to all leads.
- 3. Radius of body corner, 4 places.

1.7.3 <u>Surface Mount Package (SMD.5) - 3 terminal</u>

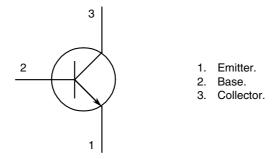


Symbols	Dimension	Notes	
	Min	Max	Notes
Α	2.84	3.15	
A1	0.25	0.51	
b	7.13	7.39	
b1	5.58	5.84	
b2	2.28	2.54	2
b3	2.92	3.18	2
D	10.03	10.28	
D1	0.76	-	2
E	7.39	7.64	
е	1.91 BSC		2



- 1. Terminal identification is specified by the components geometry where Terminal 1 = emitter, Terminal 2 = base and Terminal 3 = collector.
- 2. 2 places.

1.8 FUNCTIONAL DIAGRAM



NOTES:

- 1. For TO-39, the collector is internally connected to the case.
- 2. For TO-257, the case is not connected to any lead.
- 3. For SMD.5, the lid is not connected to any terminal.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case

For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.

For the metal flange mount package the case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.

For the surface mount package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.

b) Leads/Terminals

As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.



2.1.1 <u>Deviations from the Generic Specification</u>

2.1.1.1 Deviation from Screening Tests - Chart F3

High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.1.1.2 Deviation from Qualification and Periodic Tests - Chart F4

For SMD.5, Terminal Strength is not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.
- (d) Warning sign for Beryllium Oxide (TO-257 only)

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-39, Test Condition: E, lead fatigue.

For TO-257, Test Condition: A, tension, with an applied force of 10N for a duration of 10s.

2.4 <u>VERIFICATION OF SAFE OPERATING AREA</u>

The Safe Operating Area shall be verified as specified in the ESCC Generic Specification and Maximum Ratings herein. The test conditions shall be:

Test Method = MIL-STD-750, Method 3051, Continuous DC

 $T_{case} = +25^{\circ}C$

V_{CE}=25V

 $I_C=350mA$

Operating Time ≤ 100ms

2.5 <u>ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES</u>

Electrical measurements shall be performed at room, high and low temperatures.

2.5.1 Room Temperature Electrical Measurements

The measurements shall be performed at T_{amb} =+22 ±3°C.

Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method		Min	Max	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	3011	I _C = 100mA Bias condition D Note 1	80	-	V



ISSUE 3 - Draft A

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lir	nits	Units
		Test Method		Min	Max	
Collector-Emitter Cut-off Current	I _{CES}	3041	V _{CE} = 60V Bias condition C	-	1	μΑ
	I _{CEO}	3041	V _{CE} = 40V Bias condition D	-	50	μΑ
Emitter-Base Cut- off Current	I _{EBO1}	3061	V _{EB} =5V Bias condition D	-	1	μΑ
	I _{EBO2}	3061	V _{EB} =6V Bias condition D	-	1	mA
Forward-Current Transfer Ratio	h _{FE1}	3076	V _{CE} =5V ; I _C = 50mA Note 1	50	-	-
	h _{FE2}	3076	V _{CE} =5V ; I _C = 2.5A Note 1	70	200	-
	h _{FE3}	3076	V_{CE} =5V ; I_{C} = 5A Note 1	40	-	-
Collector-Emitter Saturation Voltage	V _{CE(sat)1}	3071	I _C =5A I _B =500mA Notes 1, 2	-	1.5	V
	V _{CE(sat)2}	3071	I _C =2.5A I _B =250mA Notes 1, 2	-	1.45	V
Base-Emitter Saturation Voltage	V _{BE(sat)1}	3066	I _C =2.5A I _B =250mA Test condition A Notes 1, 2	-	1.45	V
	V _{BE(sat)2}	3066	I _C =5A I _B =500mA Test condition A Notes 1, 2	-	2.2	V
High Frequency Small Signal Current Gain	h _{fe}	3306	V _{CE} =5V, I _C =500mA f=20MHz Note 3	3.5	-	-
Output Capacitance	C _{obo}	3236	V _{CB} =10V, I _E =0A f=1MHz Note 3	-	250	pF
Turn-on Time	t _{on}	-	$I_{C}=5A, \\ I_{B1}=500mA \\ I_{B2}=-500mA \\ V_{CC}=30V \\ V_{BB}=-4V \\ V_{IN}\approx51V \\ Notes 3, 4$	-	500	ns



ISSUE 3 - Draft A

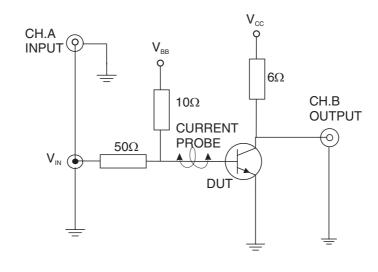


Characteristics	1	Test Conditions	Limits		Units	
		Test Method		Min	Max	
Turn-off Time	t _{off}	-	$\begin{tabular}{l l} I_{C}=5A, \\ I_{B1}=500mA \\ I_{B2}=-500mA \\ V_{CC}=30V \\ V_{BB}=-4V \\ V_{IN}\approx}51V \\ $Notes~3,~4 \\ \end{tabular}$	-	1.3	με

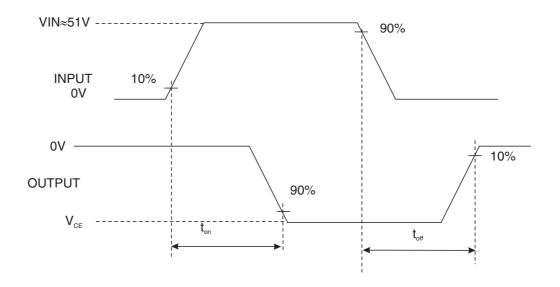
NOTES:

- 1. Pulse measurement: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
- 2. For TO-39, saturation voltages are measured 6mm from header.
- 3. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
- 4. t_{on} and t_{off} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: $t_r \leq 20$ ns, Pulse Width = 10μ s, Duty Cycle = 1%. The sampling oscilloscope for CH.A and CH.B shall have the characteristics $Z_{IN} \geq 100k\Omega$, $C_{IN} \leq 12$ pF and $t_f \leq 5$ ns. Adjustment of V_{IN} shall be made with a suitable current probe to achieve the specified I_{B1} and I_{B2} test conditions, where I_{B1} is the on-state base current and I_{B2} is the post off-state base current.





VOLTAGE WAVEFORMS



2.5.2 <u>High and Low Temperatures Electrical Measurements</u>

Characteristics	-,	MIL-STD-750	Test Conditions	Limits		Units
		Test Method	est Method Note 1	Min	Max	
Collector-Emitter Cut-off Current	I _{CES}	3041	T_{amb} =+150(+0 -5) $^{\circ}$ C V_{CE} = 60V Bias condition C	-	10	μА
Forward-Current Transfer Ratio 2	h _{FE2}	3076	T_{amb} =-55(+5 -0)°C V_{CE} =5V ; I_{C} = 2.5A Note 2	35	-	-

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures



- allowed. Alternatively a 100% inspection may be performed.
- 2. Pulse measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

2.6 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{o}$ C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift	Abso	olute	
		Value Δ	Min	Max	
Collector-Emitter Cut-off Current	I _{CES}	±100	-	1000	nA
Forward-Current Transfer Ratio 2	h _{FE2}	±25%	70	200	-
Collector-Emitter Saturation Voltage 1	V _{CE(sat)1}	±100	-	1500	mV

2.7 <u>INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS</u>

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements .

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Emitter Cut-off Current	I _{CES}	-	1	μΑ
Forward-Current Transfer Ratio 2	h _{FE2}	70	200	-
Collector-Emitter Saturation Voltage 1	V _{CE(sat)1}	-	1.5	V

2.8 POWER BURN-IN CONDITIONS

2.8.1 <u>Power Burn-in Conditions (TO-39)</u>

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+20 to +50 (1)	°C
Power Dissipation	P _{tot}	As per Maximum Ratings P _{tot1} derated at the chosen T _{amb}	W
Collector-Base Voltage	V _{CB}	20	V



1. No heat sink nor forced air directly on the device shall be permitted.

2.8.2 Power Burn-in Conditions (TO-257 and SMD.5)

Characteristics	Symbols	Conditions	Units
Case Temperature	T _{case}	+100 (+0 -5)	°C
Power Dissipation	P _{tot}	As per Maximum Ratings P _{tot2} derated at the specified T _{case}	W
Collector-Base Voltage	V _{CB}	20	V

2.9 <u>OPERATING LIFE CONDITIONS</u>

The conditions shall be as specified for Power Burn-in.



APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.